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Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

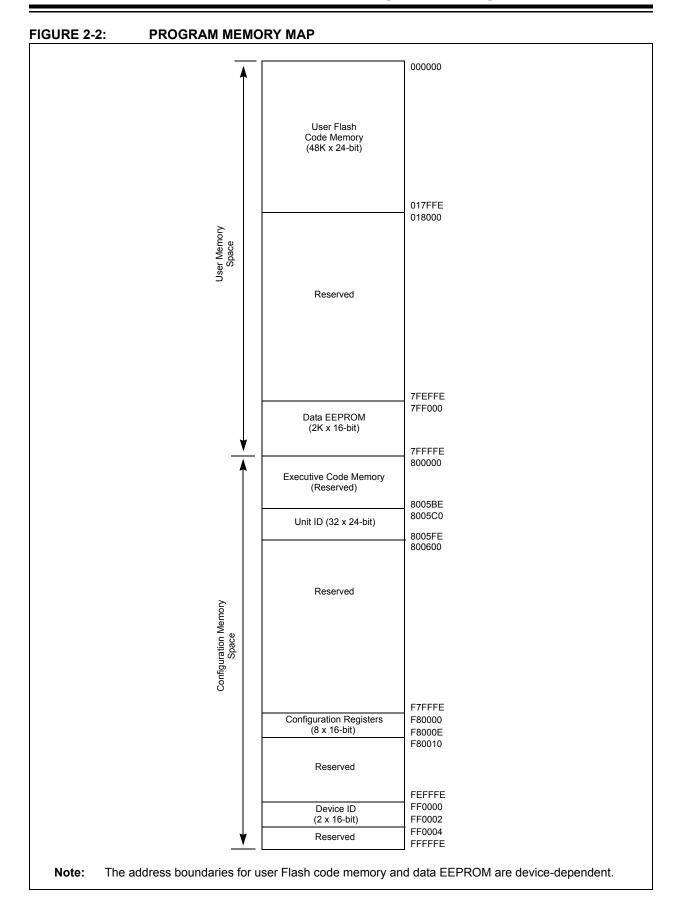
Details

E·XFI

Becano	
Product Status	Obsolete
Core Processor	dsPIC
Core Size	16-Bit
Speed	20 MIPS
Connectivity	CANbus, I ² C, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, Motor Control PWM, QEI, POR, PWM, WDT
Number of I/O	68
Program Memory Size	66KB (22K x 24)
Program Memory Type	FLASH
EEPROM Size	1K x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	2.5V ~ 5.5V
Data Converters	A/D 16x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	80-TQFP
Supplier Device Package	80-TQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/dspic30f5016t-20e-pt

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



3.0 PROGRAMMING EXECUTIVE APPLICATION

3.1 Programming Executive Overview

The programming executive resides in executive memory and is executed when Enhanced ICSP Programming mode is entered. The programming executive provides the mechanism for the programmer (host device) to program and verify the dsPIC30F, using a simple command set and communication protocol.

The following capabilities are provided by the programming executive:

- Read memory
 - Code memory and data EEPROM
 - Configuration registers
 - Device ID
- Erase memory
 - Bulk Erase by segment
 - Code memory (by row)
 - Data EEPROM (by row)
- · Program memory
 - Code memory
 - Data EEPROM
 - Configuration registers
- Query
 - Blank Device
 - Programming executive software version

The programming executive performs the low-level tasks required for erasing and programming. This allows the programmer to program the device by issuing the appropriate commands and data.

The programming procedure is outlined in **Section 5.0** "Device Programming".

3.2 Programming Executive Code Memory

The programming executive is stored in executive code memory and executes from this reserved region of memory. It requires no resources from user code memory or data EEPROM.

3.3 Programming Executive Data RAM

The programming executive uses the device's data RAM for variable storage and program execution. Once the programming executive has run, no assumptions should be made about the contents of data RAM.

4.0 CONFIRMING THE CONTENTS OF EXECUTIVE MEMORY

Before programming can begin, the programmer must confirm that the programming executive is stored in executive memory. The procedure for this task is illustrated in Figure 4-1.

First, ICSP mode is entered. The unique application ID word stored in executive memory is then read. If the programming executive is resident, the application ID word is 0xBB, which means programming can resume as normal. However, if the application ID word is not 0xBB, the programming executive must be programmed to Executive Code memory using the method described in Section 12.0 "Programming the Programming Executive to Memory".

Section 11.0 "ICSP™ Mode" describes the process for the ICSP programming method. Section 11.13 "Reading the Application ID Word" describes the procedure for reading the application ID word in ICSP mode.



CONFIRMING PRESENCE OF THE PROGRAMMING EXECUTIVE

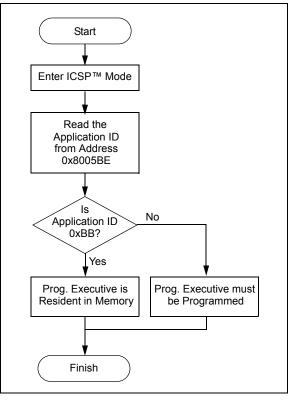


TABLE 5-5:FOSC CONFIGURATION BITS DESCRIPTION FOR dsPIC30F4011/4012 AND
dsPIC30F5011/5013

Bit Field	Register	Description
FCKSM<1:0>	FOSC	Clock Switching Mode 1x = Clock switching is disabled, Fail-Safe Clock Monitor is disabled 01 = Clock switching is enabled, Fail-Safe Clock Monitor is disabled 00 = Clock switching is enabled, Fail-Safe Clock Monitor is enabled
FOS<1:0>	FOSC	Oscillator Source Selection on POR 11 = Primary Oscillator 10 = Internal Low-Power RC Oscillator 01 = Internal Fast RC Oscillator 00 = Low-Power 32 kHz Oscillator (Timer1 Oscillator)
FPR<3:0>	FOSC	 Primary Oscillator Mode 1111 = ECIO w/PLL 16X – External Clock mode with 16X PLL. OSC2 pin is I/O 1101 = ECIO w/PLL 8X – External Clock mode with 8X PLL. OSC2 pin is I/O 1011 = ECIO w/PLL 4X – External Clock mode with 4X PLL. OSC2 pin is I/O 100 = ECIO – External Clock mode. OSC2 pin is I/O 1011 = EC – External Clock mode. OSC2 pin is system clock output (Fosc/4) 1010 = FRC w/PLL 8x – Internal fast RC oscillator with 8x PLL. OSC2 pin is I/O 1001 = ERC – External RC Oscillator mode. OSC2 pin is system clock output (Fosc/4) 1000 = ERCIO – External RC Oscillator mode. OSC2 pin is system clock output (Fosc/4) 1000 = ERCIO – External RC Oscillator mode. OSC2 pin is I/O 0111 = XT w/PLL 16X – XT Crystal Oscillator mode with 16X PLL 0101 = XT w/PLL 4X – XT Crystal Oscillator mode with 4X PLL 0101 = XT w/PLL 4X – T Crystal Oscillator mode with 4X PLL 0101 = T K w/PLL 16x – Internal fast RC oscillator with 16x PLL 0111 = ST w/PLL 4X – XT Crystal Oscillator mode with 4X PLL 0101 = KT w/PLL 16x – Internal fast RC oscillator with 16x PLL. OSC2 pin is I/O 0011 = FRC w/PLL 16x – Internal fast RC oscillator with 16x PLL. OSC2 pin is I/O 0010 = HS – HS Crystal Oscillator mode (10 MHz-25 MHz crystal) 0011 = FRC w/PLL 4x – Internal fast RC oscillator with 4x PLL. OSC2 pin is I/O 0011 = FRC w/PLL 4x – Internal fast RC oscillator with 4x PLL. OSC2 pin is I/O 0011 = FRC w/PLL 4x – Internal fast RC oscillator with 4x PLL. OSC2 pin is I/O 0011 = FRC w/PLL 4x – Internal fast RC oscillator with 4x PLL. OSC2 pin is I/O 0011 = FRC w/PLL 4x – Internal fast RC oscillator with 4x PLL. OSC2 pin is I/O 0011 = FRC w/PLL 4x – Internal fast RC oscillator with 4x PLL. OSC2 pin is I/O 0011 = FRC w/PLL 4x – Internal fast RC oscillator with 4x PLL. OSC2 pin is I/O

TABLE 5-6: FOSC CONFIGURATION BITS DESCRIPTION FOR dsPIC30F2011/2012, dsPIC30F3010/3011/3012/3013/3014, dsPIC30F4013, dsPIC30F5015/5016, dsPIC30F6010A/6011A/6012A/6013A/6014A AND dsPIC30F6015 (CONTINUED)

Bit Field	Register	Description
FPR<4:0>	FOSC	Alternate Oscillator Mode (when FOS<2:0> = 011b)
		1xxxx = Reserved (do not use)
		0111x = Reserved (do not use)
		01101 = Reserved (do not use)
		01100 = ECIO – External clock. OSC2 pin is I/O
		01011 = EC – External clock. OSC2 pin is system clock output (Fosc/4)
		01010 = Reserved (do not use)
		01001 = ERC – External RC oscillator. OSC2 pin is system clock output (Fosc/4)
		01000 = ERCIO – External RC oscillator. OSC2 pin is I/O
		00111 = Reserved (do not use)
		00110 = Reserved (do not use)
		00101 = Reserved (do not use)
		00100 = XT – XT crystal oscillator (4 MHz-10 MHz crystal)
		00010 = HS – HS crystal oscillator (10 MHz-25 MHz crystal)
		00001 = Reserved (do not use)
		00000 = XTL – XTL crystal oscillator (200 kHz-4 MHz crystal)

Bit Field	Register	Description
EBS	FBS	Boot Segment Data EEPROM Code Protection (only present in dsPIC30F5011/ 5013/6010A/6011A/6012A/6013A/6014A/6015) 1 = No Data EEPROM is reserved for Boot Segment 0 = 128 bytes of Data EEPROM are reserved for Boot Segment in dsPIC30F5011/ 5013, and 256 bytes in dsPIC30F6010A/6011A/6012A/6013A/6014A/6015
BSS<2:0>	FBS	Boot Segment Program Memory Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015) 111 = No Boot Segment 110 = Standard security; Small-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x0003FF] 101 = Standard security; Medium-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x0007FF] 100 = Standard security; Large-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x0007FF] 100 = Standard security; Large-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x001FF] 011 = No Boot Segment 010 = High security; Small-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x0003FF] 011 = High security; Medium-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x0003FF] 001 = High security; Medium-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x0007FF] 001 = High security; Large-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x0007FF] 000 = High security; Large-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x0007FF] 000 = High security; Large-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x0007FF]
BWRP	FBS	Boot Segment Program Memory Write Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015) 1 = Boot Segment program memory is not write-protected 0 = Boot Segment program memory is write-protected
RSS<1:0>	FSS	Secure Segment Data RAM Code Protection (only present in dsPIC30F5011/ 5013/6010A/6011A/6012A/6013A/6014A/6015) 11 = No Data RAM is reserved for Secure Segment 10 = Small-sized Secure RAM [(256 - N) bytes of RAM are reserved for Secure Segment] 01 = Medium-sized Secure RAM [(768 - N) bytes of RAM are reserved for Secure Segment in dsPIC30F5011/ 5013, and (2048 - N) bytes in dsPIC30F6010A/6011A/6012A/6013A/6014A/ 6015] 00 = Large-sized Secure RAM [(1024 - N) bytes of RAM are reserved for Secure Segment in dsPIC30F5011/ 5013, and (4096 - N) bytes in dsPIC30F6010A/6011A/6012A/6013A/6014A/ 6015] where N = Number of bytes of RAM reserved for Boot Sector.
ESS<1:0>	FSS	 Secure Segment Data EEPROM Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015) 11 = No Data EEPROM is reserved for Secure Segment 10 = Small-sized Secure Data EEPROM [(128 – N) bytes of Data EEPROM are reserved for Secure Segment in dsPIC30F5011/5013, and (256 – N) bytes in dsPIC30F6010A/6011A/6012A/6013A/6014A/6015] 01 = Medium-sized Secure Data EEPROM [(256 – N) bytes of Data EEPROM are reserved for Secure Segment in dsPIC30F5011/5013, and (512 – N) bytes in dsPIC30F6010A/6011A/6012A/6013A/6014A/6015] 01 = Large-sized Secure Data EEPROM [(512 – N) bytes of Data EEPROM [(512 – N) bytes of Data EEPROM are reserved for Secure Segment in dsPIC30F5011/5013, (1024 – N) bytes in dsPIC30F6011A/6013A, and (2048 – N) bytes in dsPIC30F6010A/6012A/6014A/6015]

TABLE 5-7: CONFIGURATION BITS DESCRIPTION (CONTINUED)

TABLE 5-7:	CONFIGUR	ATION BITS DESCRIPTION (CONTINUED)
Bit Field	Register	Description
SSS<2:0>	FSS	 Secure Segment Program Memory Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015) 111 = No Secure Segment 110 = Standard security; Small-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x001FFF] 101 = Standard security; Medium-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x003FFF] 100 = Standard security; Large-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x007FFF] 011 = No Secure Segment 010 = High security; Small-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x007FFF] 011 = High security; Medium-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x001FFF] 001 = High security; Medium-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x001FFF] 001 = High security; Medium-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x003FFF] 001 = High security; Medium-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x003FFF] 001 = High security; Large-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x003FFF] 000 = High security; Large-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x003FFF]
SWRP	FSS	Secure Segment Program Memory Write Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015) 1 = Secure Segment program memory is not write-protected 0 = Secure program memory is write-protected
GSS<1:0>	FGS	General Segment Program Memory Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015) 11 = Code protection is disabled 10 = Standard security code protection is enabled 0x = High security code protection is enabled
GCP	FGS	General Segment Program Memory Code Protection (present in all devices except dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015) 1 = General Segment program memory is not code-protected 0 = General Segment program memory is code-protected
GWRP	FGS	General Segment Program Memory Write Protection 1 = General Segment program memory is not write-protected 0 = General Segment program memory is write-protected
BKBUG	FICD	Debugger/Emulator Enable 1 = Device will reset into Operational mode 0 = Device will reset into Debug/Emulation mode
COE	FICD	Debugger/Emulator Enable 1 = Device will reset into Operational mode 0 = Device will reset into Clip-on Emulation mode
ICS<1:0>	FICD	ICD Communication Channel Select 11 = Communicate on PGC/EMUC and PGD/EMUD 10 = Communicate on EMUC1 and EMUD1 01 = Communicate on EMUC2 and EMUD2 00 = Communicate on EMUC3 and EMUD3
RESERVED	FBS, FSS, FGS	Reserved (read as '1', write as '1')
—	All	Unimplemented (read as '0', write as '0')

TABLE 5-7: CONFIGURATION BITS DESCRIPTION (CONTINUED)

TABLE 5-8: dsPIC30F CONFIGURATION REGISTERS (FOR dsPIC30F2010, dsPIC30F4011/4012 AND dsPIC30F6010/ 6011/6012/6013/ 6014)

Address	Name	Bit 15	Bit 14	Bit 13	Bit 12	Bit 11	Bit 10	Bit 9	Bit 8	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
0xF80000	FOSC	FCKSN	1<1:0>	—	FOS<1:0>		—	_	—	—	FPR<3:0>						
0xF80002	FWDT	FWDTEN	_	_	_	_	_	_	_	_	_	FWPS	A<1:0>	FWPSB<3:0>			
0xF80004	FBORPOR	MCLREN	_	_	_	_	PWMPIN ⁽¹⁾	HPOL ⁽¹⁾	LPOL ⁽¹⁾	BOREN	_	BORV	/<1:0>	_	— — FPWRT<1:		T<1:0>
0xF80006	FBS	—	_	Reser	ved ⁽²⁾	_	_	_	Reserved ⁽²⁾	_	_	_	_		Reserved ⁽²⁾		
0xF80008	FSS	—	_	Reser	ved ⁽²⁾	-	_	Rese	rved ⁽²⁾	—	_	_	_	Reserved ⁽²⁾			
0xF8000A	FGS	—	_	_	_	-	_	—	—	_	_	_	_	_	Reserved ⁽²⁾	GCP	GWRP
0xF8000C	FICD	BKBUG	COE	_	_	—	—	—	—	_	—	_	_	_	_	ICS<	:1:0>

 On the 6011, 6012, 6013 and 6014, these bits are reserved (read as '1' and must be programmed as '1').
 Reserved bits read as '1' and must be programmed as '1'. Note

TABLE 5-9: dsPIC30F CONFIGURATION REGISTERS (FOR dsPIC30F5011/5013)

Address	Name	Bit 15	Bit 14	Bit 13	Bit 12	Bit 11	Bit 10	Bit 9	Bit 8	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
0xF80000	FOSC	FCKSM	1<1:0>	—	—	-	_	FOS	i<1:0>	—	_	—	—		FPR<	3:0>	
0xF80002	FWDT	FWDTEN	_	_	_	—	_	_	_	_	_	FWPS	A<1:0>		FWPSE	3<3:0>	
0xF80004	FBORPOR	MCLREN	_	_	_	—	F	Reserved ⁽¹⁾		BOREN	_	BOR\	/<1:0>	—	_	FPWR	T<1:0>
0xF80006	FBS	_	_	RBS	<1:0>	_	_	—	EBS	—	_	—	—		BSS<2:0>		BWRP
0xF80008	FSS	_	_	RSS	<1:0>	_	—	ESS	<1:0>	_	_	_	_		SSS<2:0>		SWRP
0xF8000A	FGS	_		—	_	—	_	—	_	_	_	—	—	_	GSS<	1:0>	GWRP
0xF8000C	FICD	BKBUG	COE	_	_	—	_	_	_	_	_	_	_	—	_	ICS<	<1:0>

Note 1: Reserved bits read as '1' and must be programmed as '1'.

6.6 Configuration Information in the Hexadecimal File

To allow portability of code, the programmer must read the Configuration register locations from the hexadecimal file. If configuration information is not present in the hexadecimal file, a simple warning message should be issued by the programmer. Similarly, while saving a hexadecimal file, all configuration information must be included. An option to not include the configuration information can be provided.

Microchip Technology Inc. feels strongly that this feature is important for the benefit of the end customer.

6.7 Unit ID

The dsPIC30F devices contain 32 instructions of Unit ID. These are located at addresses 0x8005C0 through 0x8005FF. The Unit ID can be used for storing product information such as serial numbers, system manufacturing dates, manufacturing lot numbers and other such application-specific information.

A Bulk Erase does not erase the Unit ID locations. Instead, erase all executive memory using steps 1-4 as shown in Table 12-1, and program the Unit ID along with the programming executive. Alternately, use a Row Erase to erase the row containing the Unit ID locations.

6.8 Checksum Computation

Checksums for the dsPIC30F are 16 bits in size. The checksum is to total sum of the following:

- · Contents of code memory locations
- · Contents of Configuration registers

Table A-1 describes how to calculate the checksum for each device. All memory locations are summed one byte at a time, using only their native data size. More specifically, Configuration and device ID registers are summed by adding the lower two bytes of these locations (the upper byte is ignored), while code memory is summed by adding all three bytes of code memory.

Note: The checksum calculation differs depending on the code-protect setting. Table A-1 describes how to compute the checksum for an unprotected device and a read-protected device. Regardless of the code-protect setting, the Configuration registers can always be read.

7.0 PROGRAMMER – PROGRAMMING EXECUTIVE COMMUNICATION

7.1 Communication Overview

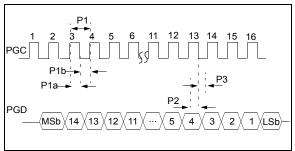
The programmer and programming executive have a master-slave relationship, where the programmer is the master programming device and the programming executive is the slave.

All communication is initiated by the programmer in the form of a command. Only one command at a time can be sent to the programming executive. In turn, the programming executive only sends one response to the programmer after receiving and processing a command. The programming executive command set is described in Section 8.0 "Programming Executive Commands". The response set is described in Section 9.0 "Programming Executive Responses".

7.2 Communication Interface and Protocol

The Enhanced ICSP interface is a 2-wire SPI interface implemented using the PGC and PGD pins. The PGC pin is used as a clock input pin, and the clock source must be provided by the programmer. The PGD pin is used for sending command data to, and receiving response data from, the programming executive. All serial data is transmitted on the falling edge of PGC and latched on the rising edge of PGC. All data transmissions are sent Most Significant bit (MSb) first, using 16-bit mode (see Figure 7-1).

FIGURE 7-1: PROGRAMMING EXECUTIVE SERIAL TIMING



Since a 2-wire SPI interface is used, and data transmissions are bidirectional, a simple protocol is used to control the direction of PGD. When the programmer completes a command transmission, it releases the PGD line and allows the programming executive to drive this line high. The programming executive keeps the PGD line high to indicate that it is processing the command.

After the programming executive has processed the command, it brings PGD low for 15 μ sec to indicate to the programmer that the response is available to be

8.0 PROGRAMMING EXECUTIVE COMMANDS

8.1 Command Set

The programming executive command set is shown in Table 8-1. This table contains the opcode, mnemonic, length, time out and description for each command. Functional details on each command are provided in the command descriptions (see Section 8.5 "Command Descriptions").

8.2 Command Format

All programming executive commands have a general format consisting of a 16-bit header and any required data for the command (see Figure 8-1). The 16-bit header consists of a 4-bit opcode field, which is used to identify the command, followed by a 12-bit command length field.

FIGURE 8-1: COMMAND FORMAT

15 12	11	0			
Opcode	Length				
Command Data First Word (if required)					
•					
•					
Command Data Last Word (if required)					

The command opcode must match one of those in the command set. Any command that is received which does not match the list in Table 8-1 will return a "NACK" response (see Section 9.2.1 "Opcode Field").

The command length is represented in 16-bit words since the SPI operates in 16-bit mode. The programming executive uses the Command Length field to determine the number of words to read from the SPI port. If the value of this field is incorrect, the command will not be properly received by the programming executive.

8.3 Packed Data Format

When 24-bit instruction words are transferred across the 16-bit SPI interface, they are packed to conserve space using the format shown in Figure 8-2. This format minimizes traffic over the SPI and provides the programming executive with data that is properly aligned for performing table write operations.

FIGURE 8-2:	PACKED INSTRUCTION
	WORD FORMAT

15	8	7	0		
lsw1					
MS	B2	MSB1			
lsw2					

Iswx: Least significant 16 bits of instruction word MSBx: Most Significant Byte of instruction word

Note:	When the number of instruction words						
	transferred is odd, MSB2 is zero and Isw2						
	cannot be transmitted.						

8.4 Programming Executive Error Handling

The programming executive will "NACK" all unsupported commands. Additionally, due to the memory constraints of the programming executive, no checking is performed on the data contained in the Programmer command. It is the responsibility of the programmer to command the programming executive with valid command arguments, or the programming operation may fail. Additional information on error handling is provided in Section 9.2.3 "QE_Code Field".

8.5 Command Descriptions

All commands that are supported by the programming executive are described in Section 8.5.1 "SCHECK Command" through Section 8.5.11 "QVER Command".

8.5.1 SCHECK COMMAND

15	12	11 0)
	Opcode	Length	

Field	Description
Opcode	0x0
Length	0x1

The SCHECK command instructs the programming executive to do nothing, but generate a response. This command is used as a "sanity check" to verify that the programming executive is operational.

Expected Response (2 words):

0x1000 0x0002

Note: This instruction is not required for programming, but is provided for development purposes only.

8.5.2 READD COMMAND

15	12	11	8	7	0
Орс	ode			Length	
Reser	ved0			Ν	
	Reser	ved1		Addr_MSB	
			Addr_	LS	

Field	Description
Opcode	0x1
Length	0x4
Reserved0	0x0
N	Number of 16-bit words to read (max of 2048)
Reserved1	0x0
Addr_MSB	MSB of 24-bit source address
Addr_LS	LS 16 bits of 24-bit source address

The READD command instructs the programming executive to read N 16-bit words of memory starting from the 24-bit address specified by Addr_MSB and Addr_LS. This command can only be used to read 16-bit data. It can be used to read data EEPROM, Configuration registers and the device ID.

Expected Response (2+N words):

0x1100 N + 2 Data word 1

Data word N

Note: Reading unimplemented memory will cause the programming executive to reset.

10.0 DEVICE ID

The device ID region is 2×16 bits and can be read using the READD command. This region of memory is read-only and can also be read when code protection is enabled.

Table 10-1shows the device ID for each device,Table 10-2shows the device ID registers and Table 10-33describes the bit field of each register.

Device					Silicon I	Revision			
Device	DEVID	A0	A1	A2	A3	A4	В0	B1	B2
dsPIC30F2010	0x0040	0x1000	0x1001	0x1002	0x1003	0x1004	—	—	—
dsPIC30F2011	0x0240	_	0x1001				_	_	_
dsPIC30F2012	0x0241	_	0x1001	_	_	_	_	_	_
dsPIC30F3010	0x01C0	0x1000	0x1001	0x1002	—	—	_	—	—
dsPIC30F3011	0x01C1	0x1000	0x1001	0x1002	_		—	—	—
dsPIC30F3012	0x00C1	_	_	_	_	_	0x1040	0x1041	_
dsPIC30F3013	0x00C3	—	_	—	—	—	0x1040	0x1041	—
dsPIC30F3014	0x0160	_	0x1001	0x1002	_	_	_	_	_
dsPIC30F4011	0x0101	_	0x1001	0x1002	0x1003	0x1003	_	_	_
dsPIC30F4012	0x0100	—	0x1001	0x1002	0x1003	0x1003	—	—	—
dsPIC30F4013	0x0141	—	0x1001	0x1002	_	_	_	—	—
dsPIC30F5011	0x0080	_	0x1001	0x1002	0x1003	0x1003	_	_	_
dsPIC30F5013	0x0081	_	0x1001	0x1002	0x1003	0x1003	_	_	_
dsPIC30F5015	0x0200	0x1000	_	_	_		_	—	—
dsPIC30F5016	0x0201	0x1000	_	_	_	_	_	_	_
dsPIC30F6010	0x0188	_	_	_	_		_	0x1040	0x1042
dsPIC30F6010A	0x0281	_	_	0x1002	0x1003	0x1004	_	_	_
dsPIC30F6011	0x0192	_	_	_	0x1003	_	_	0x1040	0x1042
dsPIC30F6011A	0x02C0	—	_	0x1002	—	—	0x1040	0x1041	—
dsPIC30F6012	0x0193	—	_	_	0x1003		—	0x1040	0x1042
dsPIC30F6012A	0x02C2	—	_	0x1002	_		0x1040	0x1041	—
dsPIC30F6013	0x0197	_	_	_	0x1003		_	0x1040	0x1042
dsPIC30F6013A	0x02C1			0x1002			0x1040	0x1041	_
dsPIC30F6014	0x0198				0x1003			0x1040	0x1042
dsPIC30F6014A	0x02C3	—		0x1002	_	_	0x1040	0x1041	—
dsPIC30F6015	0x0280	_	_	0x1002	0x1003	0x1004	_	_	

TABLE 10-1:	DEVICE IDS
IABLE 10-1:	

TABLE 10-2: dsPIC30F DEVICE ID REGISTERS

Address	Nama								В	it							
Address	Name	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
0xFF0000	DEVID							D	EVID	<15:0	>						
0xFF0002	DEVREV	F	PROC	<3:0>	>			REV	<5:0>					DOT	<5:0>		

11.4 Flash Memory Programming in ICSP Mode

Programming in ICSP mode is described in Section 11.4.1 "Programming Operations" through Section 11.4.3 "Starting and Stopping a Programming Cycle". Step-by-step procedures are described in Section 11.5 "Erasing Program Memory in Normal-Voltage Systems" through Section 11.13 "Reading the Application ID Word". All programming operations must use serial execution, as described in Section 11.2 "ICSP Operation".

11.4.1 PROGRAMMING OPERATIONS

Flash memory write and erase operations are controlled by the NVMCON register. Programming is performed by setting NVMCON to select the type of erase operation (Table 11-2) or write operation (Table 11-3), writing a key sequence to enable the programming and initiating the programming by setting the WR control bit, NVMCON<15>.

In ICSP mode, all programming operations are externally timed. An external 2 ms delay must be used between setting the WR control bit and clearing the WR control bit to complete the programming operation.

TABLE 11-2: NVMCON ERASE OPERATIONS

NVMCON Value	Erase Operation
0x407F	Erase all code memory, data memory (does not erase UNIT ID).
0x4075	Erase 1 row (16 words) of data EEPROM.
0x4074	Erase 1 word of data EEPROM.
0x4072	Erase all executive memory.
0x4071	Erase 1 row (32 instruction words) from 1 panel of code memory.
0x406E	Erase Boot Secure and General Segments, then erase FBS, FSS and FGS configuration registers.
0x4066	Erase all Data EEPROM allocated to Boot Segment.
0x405E	Erase Secure and General Segments, then erase FSS and FGS configuration registers.
0x4056	Erase all Data EEPROM allocated to Secure Segment.
0x404E	Erase General Segment, then erase FGS configuration register.
0x4046	Erase all Data EEPROM allocated to General Segment.

TABLE 11-3: NVMCON WRITE OPERATIONS

NVMCON Value	Write Operation
0x4008	Write 1 word to configuration
	memory.
0x4005	Write 1 row (16 words) to data memory.
0x4004	Write 1 word to data memory.
0x4001	Write 1 row (32 instruction words) into 1 panel of program memory.

11.4.2 UNLOCKING NVMCON FOR PROGRAMMING

Writes to the WR bit (NVMCON<15>) are locked to prevent accidental programming from taking place. Writing a key sequence to the NVMKEY register unlocks the WR bit and allows it to be written to. The unlock sequence is performed as follows:

MOV	#0x55, W8
MOV	W8, NVMKEY
MOV	#OxAA, W9
MOV	W9, NVMKEY
Note:	Any working register, or working register pair, can be used to write the unlock sequence.

11.4.3 STARTING AND STOPPING A PROGRAMMING CYCLE

Once the unlock key sequence has been written to the NVMKEY register, the WR bit (NVMCON<15>) is used to start and stop an erase or write cycle. Setting the WR bit initiates the programming cycle. Clearing the WR bit terminates the programming cycle.

All erase and write cycles must be externally timed. An external delay must be used between setting and clearing the WR bit. Starting and stopping a programming cycle is performed as follows:

BSET	NVMCON,	#WR
<wait< td=""><td>2 ms></td><td></td></wait<>	2 ms>	
BCLR	NVMCON,	#WR

11.5 Erasing Program Memory in Normal-Voltage Systems

The procedure for erasing program memory (all code memory, data memory, executive memory and codeprotect bits) consists of setting NVMCON to 0x407F, unlocking NVMCON for erasing and then executing the programming cycle. This method of bulk erasing program memory only works for systems where VDD is between 4.5 volts and 5.5 volts. The method for erasing program memory for systems with a lower VDD (3.0 volts-4.5 volts) is described in Section 6.1 "Erasing Memory". Table 11-4 shows the ICSP programming process for bulk-erasing program memory. This process includes the ICSP command code, which must be transmitted (for each instruction) to the Least Significant bit first using the PGC and PGD pins (see Figure 11-2).

If an individual Segment Erase operation is required, the NVMCON value must be replaced by the value for the corresponding Segment Erase operation.

Note:	Program memory must be erased before
	writing any data to program memory.

TABLE 11-4:SERIAL INSTRUCTION EXECUTION FOR BULK ERASING PROGRAM MEMORY
(ONLY IN NORMAL-VOLTAGE SYSTEMS)

08A 80A	GOTO 0x100 GOTO 0x100 NOP the FBS Configuration register. ⁽¹⁾ MOV #0x4008, W10 MOV W10, NVMCON
00 000 DN to program 08A 00A TBLPAG and	GOTO 0×100 NOP the FBS Configuration register. ⁽¹⁾ MOV #0×4008, W10
DN to program	NOP the FBS Configuration register. ⁽¹⁾ MOV #0x4008, W10
DN to program	the FBS Configuration register. ⁽¹⁾
BA BOA CHANNE TBLPAG and	MOV #0x4008, W10
BOA TBLPAG and	
e TBLPAG and	MOV W10, NVMCON
'80	write pointer (W7) for TBLWT instruction for Configuration register. ⁽¹⁾
	MOV #0xF8, W0
.90	MOV W0, TBLPAG
67	MOV #0x6, W7
onfiguration Re	egister data to W6. ⁽¹⁾
300	CLR W6
000	NOP
onfiguration Re	egister write latch. Advance W7 to point to next Configuration register. ⁽¹⁾
386	TBLWTL W6, [W7++]
NVMCON for p	programming the Configuration register. ⁽¹⁾
58	MOV #0x55, W8
A9	MOV #0xAA, W9
338	MOV W8, NVMKEY
339	MOV W9, NVMKEY
orogramming c	ycle. ⁽¹⁾
61	BSET NVMCON, #WR
000	NOP
000	NOP
	Externally time 2 ms
000	NOP
000	NOP
61	BCLR NVMCON, #WR
000	NOP
000	NOP
os 5-7 one time	e to program 0x0000 to RESERVED2 Configuration register. ⁽¹⁾
VICON to erase	e all Program Memory.
'FA	MOV #0x407F, W10
30A	MOV W10, NVMCON
O OS M	5-7 one time CON to erase

Note 1: Steps 2-8 are only required for the dsPIC30F5011/5013 devices. These steps may be skipped for all other devices in the dsPIC30F family.

TABLE 11-5:SERIAL INSTRUCTION EXECUTION FOR ERASING PROGRAM MEMORY
(EITHER IN LOW-VOLTAGE OR NORMAL-VOLTAGE SYSTEMS) (CONTINUED)

Command (Binary)	Data (Hexadecimal)	Description
• •		stored in NVMADRU:NVMADR. When W6 rolls over to 0x0, NVMADRU must be
incre	emented.	
0000	430307	ADD W6, W7, W6
0000	AF0042	BTSC SR, #C
0000	EC2764	INC NVMADRU
0000	883B16	MOV W6, NVMADR
Step 7: Res	et device internal PC	J
0000	040100	GOTO 0x100
0000	000000	NOP
Step 8: Rep	eat Steps 3-7 until a	all rows of code memory are erased.
Step 9: Initia	alize NVMADR and I	NVMADRU to erase executive memory and initialize W7 for row address updates.
	EB0300	CLR W6
0000	883B16	MOV W6, NVMADR
0000	200807	MOV #0x80, W7
0000	883B27	MOV W7, NVMADRU
0000	200407	MOV #0x40, W7
Step 10: Se	t NVMCON to erase	e 1 row of executive memory.
0000	24071A	MOV #0x4071, W10
0000	883B0A	MOV W10, NVMCON
Step 11: Un	lock the NVMCON to	o erase 1 row of executive memory.
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
Step 12: Init	tiate the erase cycle.	
0000	A8E761	BSET NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
_	-	Externally time 'P13a' ms (see Section 13.0 "AC/DC Characteristics and
0000	000000	Timing Requirements") NOP
0000	000000	NOP
	00000	NOP
	000000 A9E761	NOP BCLR NVMCON, #WR
0000		NOP BCLR NVMCON, #WR NOP
0000 0000	A9E761	BCLR NVMCON, #WR
0000 0000 0000	A9E761 000000 000000	BCLR NVMCON, #WR NOP
0000 0000 0000	A9E761 000000 000000	BCLR NVMCON, #WR NOP NOP ss stored in NVMADR.
0000 0000 0000 Step 13: Up	A9E761 000000 000000 date the row addres	BCLR NVMCON, #WR NOP NOP
0000 0000 Step 13: Up 0000 0000	A9E761 000000 odate the row addres 430307 883B16	BCLR NVMCON, #WR NOP NOP SS Stored in NVMADR. ADD W6, W7, W6 MOV W6, NVMADR
0000 0000 Step 13: Up 0000 0000 Step 14: Re	A9E761 000000 odate the row addres 430307 883B16 eset device internal P	BCLR NVMCON, #WR NOP NOP SS stored in NVMADR. ADD W6, W7, W6 MOV W6, NVMADR PC.
0000 0000 Step 13: Up 0000 0000 Step 14: Re	A9E761 000000 odate the row addres 430307 883B16 eset device internal F 040100	BCLR NVMCON, #WR NOP NOP SS Stored in NVMADR. ADD W6, W7, W6 MOV W6, NVMADR
0000 0000 Step 13: Up 0000 Step 14: Re 0000 0000	A9E761 000000 date the row addres 430307 883B16 set device internal F 040100 00000	BCLR NVMCON, #WR NOP NOP SS stored in NVMADR. ADD W6, W7, W6 MOV W6, NVMADR PC: GOTO 0x100 NOP
2000 2000 Step 13: Up 2000 2000 Step 14: Re 2000 2000 Step 15: Re	A9E761 000000 date the row addres 430307 883B16 eset device internal F 040100 000000 epeat Steps 10-14 un	BCLR NVMCON, #WR NOP NOP SS Stored in NVMADR. ADD W6, W7, W6 MOV W6, NVMADR PC. GOTO 0x100 NOP stil all 24 rows of executive memory are erased.
2000 2000 Step 13: Up 2000 2000 Step 14: Re 2000 2000 Step 15: Re Step 16: Init	A9E761 000000 odate the row addres 430307 883B16 set device internal F 040100 00000 peat Steps 10-14 un tialize NVMADR and	BCLR NVMCON, #WR NOP NOP SS stored in NVMADR. ADD W6, W7, W6 MOV W6, NVMADR PC. GOTO 0×100 NOP ntil all 24 rows of executive memory are erased.
2000 2000 Step 13: Up 2000 Step 14: Re 2000 2000 Step 15: Re Step 16: Init	A9E761 000000 odate the row addres 430307 883B16 set device internal F 040100 000000 peat Steps 10-14 un tialize NVMADR and 2xxxx6	BCLR NVMCON, #WR NOP NOP SS stored in NVMADR. ADD W6, W7, W6 MOV W6, NVMADR PC. GOTO 0x100 NOP ntil all 24 rows of executive memory are erased. MVWADRU to erase data memory and initialize W7 for row address updates. MOV # <lower 16-bits="" address="" data="" eeprom="" of="" starting="">, W6</lower>
0000 0000 Step 13: Up 0000 Step 14: Re 0000 Step 15: Re Step 16: Init 0000 0000	A9E761 000000 odate the row addres 430307 883B16 set device internal F 040100 00000 opeat Steps 10-14 un tialize NVMADR and 2XXXX6 883B16	BCLR NVMCON, #WR NOP NOP SS stored in NVMADR. ADD W6, W7, W6 MOV W6, NVMADR PC. GOTO 0x100 NOP ntil all 24 rows of executive memory are erased. MVMADRU to erase data memory and initialize W7 for row address updates. MOV # <lower 16-bits="" address="" data="" eeprom="" of="" starting="">, W6 MOV W6, NVMADR</lower>
0000 0000 Step 13: Up 0000 Step 14: Re 0000 Step 15: Re Step 16: Init 0000 0000 0000 0000 0000	A9E761 000000 odate the row addres 430307 883B16 set device internal F 040100 000000 peat Steps 10-14 un tialize NVMADR and 2xxxx6	BCLR NVMCON, #WR NOP NOP SS stored in NVMADR. ADD W6, W7, W6 MOV W6, NVMADR PC. GOTO 0x100 NOP ntil all 24 rows of executive memory are erased. MVMADRU to erase data memory and initialize W7 for row address updates. MOV # <lower 16-bits="" address="" data="" eeprom="" of="" starting="">, W6 MOV #0x7F, W6</lower>
0000 0000 Step 13: Up 0000 Step 14: Re 0000 Step 15: Re Step 16: Init	A9E761 000000 odate the row addres 430307 883B16 set device internal F 040100 000000 peat Steps 10-14 un tialize NVMADR and 2XXXX6 883B16 2007F6	BCLR NVMCON, #WR NOP NOP SS stored in NVMADR. ADD W6, W7, W6 MOV W6, NVMADR PC. GOTO 0x100 NOP ntil all 24 rows of executive memory are erased. MVMADRU to erase data memory and initialize W7 for row address updates. MOV # <lower 16-bits="" address="" data="" eeprom="" of="" starting="">, W6 MOV W6, NVMADR MOV #0x7F, W6</lower>
0000 0000 Step 13: Up 0000 Step 14: Re 0000 Step 15: Re Step 16: Init 0000 0000 0000 0000 0000 0000 0000 0000 0000	A9E761 000000 odate the row address 430307 883B16 eset device internal F 040100 000000 epeat Steps 10-14 un tialize NVMADR and 2XXXX6 883B16 2007F6 883B16 200207	BCLR NVMCON, #WR NOP SS stored in NVMADR. ADD W6, W7, W6 MOV W6, NVMADR PC. GOTO 0x100 NOP ntil all 24 rows of executive memory are erased. MVMADRU to erase data memory and initialize W7 for row address updates. MOV # <lower 16-bits="" address="" data="" eeprom="" of="" starting="">, W6 MOV #0x7F, W6 MOV #0x7F, W6 MOV #0x20, W7</lower>
0000 0000 Step 13: Up 0000 Step 14: Re 0000 Step 15: Re Step 16: Init 0000 0000 0000 0000 0000 0000 0000 0000 0000	A9E761 000000 odate the row address 430307 883B16 eset device internal F 040100 000000 epeat Steps 10-14 un tialize NVMADR and 2XXXX6 883B16 2007F6 883B16 200207	BCLR NVMCON, #WR NOP SS stored in NVMADR. ADD W6, W7, W6 MOV W6, NVMADR PC. GOTO 0x100 NOP ntil all 24 rows of executive memory are erased. MVWADRU to erase data memory and initialize W7 for row address updates. MOV # <lower 16-bits="" address="" data="" eeprom="" of="" starting="">, W6 MOV #0x7F, W6 MOV #0x7F, W6 MOV W6, NVMADR</lower>

(Binary)	Data (Hexadecimal)	Description
	ne read pointer (W6) and load the (next set of) write latches.
0000	EB0300	CLR W6
0000	000000	NOP
0000	BB0BB6	TBLWTL [W6++], [W7]
0000	000000	NOP
0000	000000	NOP
0000	BBDBB6	TBLWTH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BBEBB6	TBLWTH.B [W6++], [++W7]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB0BB6	TBLWTL [W6++], [W7]
0000	000000	NOP
0000	000000	NOP
0000	BBDBB6	TBLWTH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BBEBB6	TBLWTH.B [W6++], [++W7]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
Step 6: Repe	at steps 4-5 eight ti	mes to load the write latches for 32 instructions.
Step 7: Unloc	ck the NVMCON for	writing.
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
Stop 8: Initia	te the write cycle.	
Step 6. millia		
	A8E761	BSET NVMCON, #WR
0000		BSET NVMCON, #WR NOP
0000	000000	
0000 0000 0000		NOP NOP
0000 0000 0000	000000 000000	NOP NOP Externally time 'P12a' ms (see Section 13.0 "AC/DC Characteristics and
0000 0000 0000 	000000 000000	NOP NOP
0000 0000 0000 	000000 000000 - 000000	NOP NOP Externally time 'P12a' ms (see Section 13.0 "AC/DC Characteristics and Timing Requirements") NOP
0000 0000 0000 0000 0000	000000 000000 - 000000 000000	NOP NOP Externally time 'P12a' ms (see Section 13.0 "AC/DC Characteristics and Timing Requirements") NOP NOP
0000 0000 	000000 000000 - 000000 000000 A9E761	NOP NOP Externally time 'P12a' ms (see Section 13.0 "AC/DC Characteristics and Timing Requirements") NOP
0000 0000 0000 	000000 000000 - 000000 000000	NOP NOP Externally time 'P12a' ms (see Section 13.0 "AC/DC Characteristics and Timing Requirements") NOP NOP BCLR NVMCON, #WR NOP
0000 0000 	000000 000000 - 000000 A9E761 000000 000000	NOP NOP Externally time 'P12a' ms (see Section 13.0 "AC/DC Characteristics and Timing Requirements") NOP NOP BCLR NVMCON, #WR NOP NOP
0000 0000 	000000 000000 - 000000 000000 A9E761 000000 000000 t device internal PC	NOP NOP Externally time 'P12a' ms (see Section 13.0 "AC/DC Characteristics and Timing Requirements") NOP NOP BCLR NVMCON, #WR NOP NOP
0000 0000 	000000 000000 - 000000 A9E761 000000 000000	NOP NOP Externally time 'P12a' ms (see Section 13.0 "AC/DC Characteristics and Timing Requirements") NOP NOP BCLR NVMCON, #WR NOP NOP

TABLE 11-8: SERIAL INSTRUCTION EXECUTION FOR WRITING CODE MEMORY (CONTINUED)

11.12 Reading Data Memory

The procedure for reading data memory is similar to that of reading code memory, except that 16-bit data words are read instead of 24-bit words. Since less data is read in each operation, only working registers W0:W3 are used as temporary holding registers for the data to be read.

Table 11-12 shows the ICSP programming details for reading data memory. Note that the TBLPAG register is hard-coded to 0x7F (the upper byte address of all locations of data memory).

TABLE 11-12: SERIAL INSTRUCTION EXECUTION FOR READING DATA MEMORY

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit t	he Reset vector.	
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
Step 2: Initial	ize TBLPAG and	the read pointer (W6) for TBLRD instruction.
0000	2007F0	MOV #0x7F, WO
0000	880190	MOV W0, TBLPAG
0000	2xxxx6	MOV # <sourceaddress15:0>, W6</sourceaddress15:0>
Step 3: Initial		er (W7) and store the next four locations of code memory to W0:W5.
0000	EB0380	CLR W7
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
Step 4: Outp	ut W0:W5 using th	ne VISI register and REGOUT command.
0000	883C20	MOV W0, VISI
0000	000000	NOP
0001	<visi></visi>	Clock out contents of VISI register
0000	000000	NOP
0000	883C21	MOV W1, VISI
0000	000000	NOP
0001	<visi></visi>	Clock out contents of VISI register
0000	000000	NOP
0000	883C22	MOV W2, VISI
0000	000000	NOP
0001	<visi></visi>	Clock out contents of VISI register
0000	000000	NOP
0000	883C23	MOV W3, VISI
0000	000000	NOP
0001	<visi></visi>	Clock out contents of VISI register
0000	000000	NOP
Step 5: Rese	t device internal F	PC.
0000	040100	GOTO 0x100
0000	000000	NOP

(Binary)	d Data (Hexadecim	Description
	•	/W6) and load the (next four write) latches.
•		
0000 0000	EB0300 000000	CLR W6 NOP
0000		
	BB0BB6 000000	TBLWTL [W6++], [W7]
0000		NOP
0000	000000	NOP TBLWTH.B [W6++], [W7++]
0000	BBDBB6	
0000	000000	NOP
0000	000000 BBEBB6	
0000	-	TBLWTH.B [W6++], [++W7]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB0BB6	TBLWTL [W6++], [W7]
0000	000000	NOP
0000	000000	NOP
0000	BBDBB6	TBLWTH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BBEBB6	TBLWTH.B [W6++], [++W7]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
		ht times to load the write latches for the 32 instructions.
Step 10: 0		N for programming.
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
		ming cycle
Step 11: In	itiate the programr	
-	A8E761	BSET NVMCON, #15
0000		
0000	A8E761	BSET NVMCON, #15
0000 0000 0000	A8E761 000000	BSET NVMCON, #15 NOP
0000 0000 0000	A8E761 000000 000000	BSET NVMCON, #15 NOP NOP Externally time 'P12a' ms (see Section 13.0 "AC/DC Characteristics and
-	A8E761 000000 000000	BSET NVMCON, #15 NOP NOP
- 0000 0000 - 0000	A8E761 000000 000000 -	BSET NVMCON, #15 NOP NOP Externally time 'P12a' ms (see Section 13.0 "AC/DC Characteristics and Timing Requirements")
0000 0000 0000 	A8E761 000000 000000 - 000000	BSET NVMCON, #15 NOP NOP Externally time `P12a' ms (see Section 13.0 "AC/DC Characteristics and Timing Requirements") NOP
0000 0000 	A8E761 000000 000000 - 000000 000000	BSET NVMCON, #15 NOP NOP Externally time `P12a' ms (see Section 13.0 "AC/DC Characteristics and Timing Requirements") NOP NOP
Step 11: In 0000 0000 0000 	A8E761 000000 000000 - 000000 000000 A9E761	BSET NVMCON, #15 NOP NOP Externally time 'P12a' ms (see Section 13.0 "AC/DC Characteristics and Timing Requirements") NOP NOP BCLR NVMCON, #15
0000 0000 	A8E761 000000 000000 - 000000 000000 A9E761 000000	BSET NVMCON, #15 NOP NOP Externally time 'P12a' ms (see Section 13.0 "AC/DC Characteristics and Timing Requirements") NOP NOP BCLR NVMCON, #15 NOP NOP
0000 0000 	A8E761 000000 000000 - 000000 000000 A9E761 000000 000000	BSET NVMCON, #15 NOP NOP Externally time 'P12a' ms (see Section 13.0 "AC/DC Characteristics and Timing Requirements") NOP NOP BCLR NVMCON, #15 NOP NOP

TABLE 12-1: PROGRAMMING THE PROGRAMMING EXECUTIVE (CONTINUED)

APPENDIX A: DEVICE-SPECIFIC INFORMATION

A.1 Checksum Computation

The checksum computation is described in **Section 6.8 "Checksum Computation"**. Table A-1 shows how this 16-bit computation can be made for each dsPIC30F device. Computations for read code protection are shown both enabled and disabled. The checksum values assume that the Configuration registers are also erased. However, when code protection is enabled, the value of the FGS register is assumed to be 0x5.

A.2 dsPIC30F5011 and dsPIC30F5013

A.2.1 ICSP PROGRAMMING

The dsPIC30F5011 and dsPIC30F5013 processors require that the FBS and FSS registers be programmed with 0x0000 before the device is chip erased. The steps to perform this action are shown in Table 11-4.

A.2.2 ENHANCED ICSP PROGRAMMING

The dsPIC30F5011 and dsPIC30F5013 processors require that the FBS and FSS registers be programmed with 0x0000 using the PROGC command before the ERASEB command is used to erase the chip.

Device	Read Code Protection	Checksum Computation	Erased Value	Value with 0xAAAAAA at 0x0 and Last Code Address
dsPIC30F2010	Disabled	CFGB+SUM(0:001FFF)	0xD406	0xD208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F2011	Disabled	CFGB+SUM(0:001FFF)	0xD406	0xD208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F2012	Disabled	CFGB+SUM(0:001FFF)	0xD406	0xD208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F3010	Disabled	CFGB+SUM(0:003FFF)	0xA406	0xA208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F3011	Disabled	CFGB+SUM(0:003FFF)	0xA406	0xA208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F3012	Disabled	CFGB+SUM(0:003FFF)	0xA406	0xA208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F3013	Disabled	CFGB+SUM(0:003FFF)	0xA406	0xA208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F3014	Disabled	CFGB+SUM(0:003FFF)	0xA406	0xA208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F4011	Disabled	CFGB+SUM(0:007FFF)	0x4406	0x4208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F4012	Disabled	CFGB+SUM(0:007FFF)	0x4406	0x4208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F4013	Disabled	CFGB+SUM(0:007FFF)	0x4406	0x4208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F5011	Disabled	CFGB+SUM(0:00AFFF)	0xFC06	0xFA08
	Enabled	CFGB	0x0404	0x0404
dsPIC30F5013	Disabled	CFGB+SUM(0:00AFFF)	0xFC06	0xFA08
	Enabled	CFGB	0x0404	0x0404
dsPIC30F5015	Disabled	CFGB+SUM(0:00AFFF)	0xFC06	0xFA08
	Enabled	CFGB	0x0404	0x0404

TABLE A-1: CHECKSUM COMPUTATION

Item Description:

SUM(a:b) = Byte sum of locations a to b inclusive (all 3 bytes of code memory)

CFGB = Configuration Block (masked) = Byte sum of ((FOSC&0xC10F) + (FWDT&0x803F) + (FBORPOR&0x87B3) + (FBS&0x310F) + (FSS&0x330F) + (FGS&0x0007) + (FICD&0xC003))

APPENDIX B: HEX FILE FORMAT

Flash programmers process the standard HEX format used by the Microchip development tools. The format supported is the Intel[®] HEX 32 Format (INHX32). Please refer to Appendix A in the "*MPASM User's Guide*" (DS33014) for more information about hex file formats.

The basic format of the hex file is:

:ВВААААТТНННН...ННННСС

Each data record begins with a 9-character prefix and always ends with a 2-character checksum. All records begin with ':' regardless of the format. The individual elements are described below.

- BB is a two-digit hexadecimal byte count representing the number of data bytes that appear on the line. Divide this number by two to get the number of words per line.
- AAAA is a four-digit hexadecimal address representing the starting address of the data record. Format is high byte first followed by low byte. The address is doubled because this format only supports 8-bits. Divide the value by two to find the real device address.
- TT is a two-digit record type that will be '00' for data records, '01' for end-of-file records and '04' for extended-address record.
- HHHH is a four-digit hexadecimal data word. Format is low byte followed by high byte. There will be BB/2 data words following TT.
- CC is a two-digit hexadecimal checksum that is the two's complement of the sum of all the preceding bytes in the line record.

Because the Intel hex file format is byte-oriented, and the 16-bit program counter is not, program memory sections require special treatment. Each 24-bit program word is extended to 32 bits by inserting a socalled "phantom byte". Each program memory address is multiplied by 2 to yield a byte address.

As an example, a section that is located at 0x100 in program memory will be represented in the hex file as 0x200.

The hex file will be produced with the following contents:

:020000040000fa

:040200003322110096

:0000001FF

Notice that the data record (line 2) has a load address of 0200, while the source code specified address 0x100. Note also that the data is represented in "littleendian" format, meaning the Least Significant Byte (LSB) appears first. The phantom byte appears last, just before the checksum.



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